MBR2535CTG, MBR2545CTG

Power Rectifiers

The MBR2535CT/45CT series uses the Schottky Barrier principle with a platinum barrier metal. These state-of-the-art devices have the following features:

Features

- Guardring for Stress Protection
- Low Forward Voltage
- 175°C Operating Junction Temperature
- These are Pb-Free Devices*

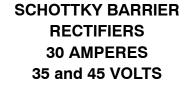
Mechanical Characteristics

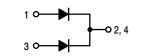
- Case: Epoxy, Molded
- Epoxy Meets UL 94 V-0 @ 0.125 in
- Weight: 1.9 grams (approximately)
- Finish: All External Surfaces Corrosion Resistant and Terminal Leads are Readily Solderable
- Lead Temperature for Soldering Purposes: 260°C Max. for 10 Seconds



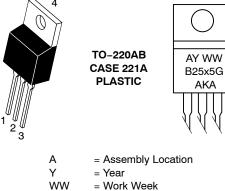
ON Semiconductor®

http://onsemi.com





MARKING DIAGRAM



B25x5	= Device Cod

= Device Code

х

G

- = 3 or 4 = Pb-Free Package
- = Diode Polarity AKA

ORDERING INFORMATION

Device	Package	Shipping
MBR2535CTG	TO–220 (Pb–Free)	50 Units/Rail
MBR2545CTG	TO-220 (Pb-Free)	50 Units/Rail

*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

MBR2535CTG, MBR2545CTG

MAXIMUM RATINGS

Rating		Symbol	Value	Unit
	MBR2535CT MBR2545CT	V _{RRM} V _{RWM} V _R	35 45	V
Average Rectified Forward Current (Rated V_R , T_C = 160°C)	Per Device Per Diode	I _{F(AV)}	30 15	A
Peak Repetitive Forward Current, per Diode Leg (Rated V_R , Square Wave, 20 kHz, $T_C = 150^{\circ}C$)		I _{FRM}	30	A
Non-Repetitive Peak Surge Current per Diode Leg (Surge Applied at Rated Load Conditions, Halfwave, Single Ph	ase, 60 Hz)	I _{FSM}	150	A
Peak Repetitive Reverse Surge Current (2.0 $\mu s,$ 1.0 kHz)		I _{RRM}	1.0	А
Storage Temperature Range		T _{stg}	-65 to +175	°C
Operating Junction Temperature (Note 1)		ТJ	-65 to +175	°C
Voltage Rate of Change (Rated V _R)		dv/dt	10,000	V/μs
ESD Ratings: Machine Model = C Human Body Model = 3B		ESD	>400 >8000	V

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

1. The heat generated must be less than the thermal conductivity from Junction-to-Ambient: $dP_D/dT_J < 1/R_{\theta JA}$.

THERMAL CHARACTERISTICS (Per Leg)

Characteristic	Symbol	Value	Unit
Thermal Resistance, – Junction-to-Case – Junction-to-Ambient (Note 2)	$R_{ heta JC}$ $R_{ heta JA}$	1.5 50	°C/W

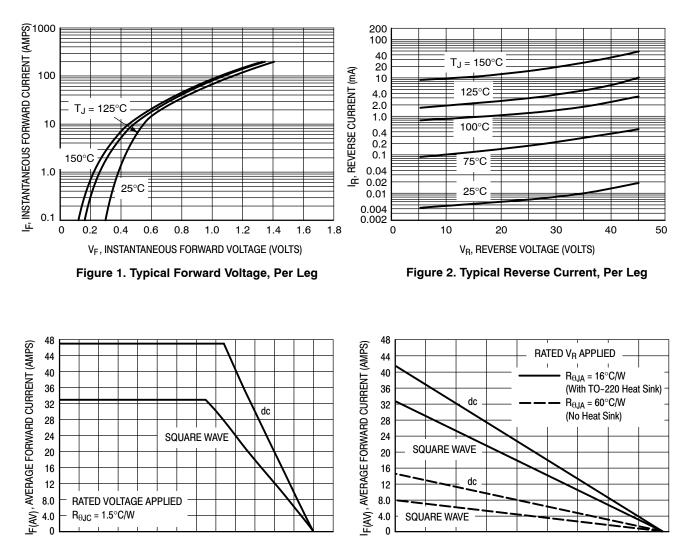
2. When mounted using minimum recommended pad size on FR-4 board.

ELECTRICAL CHARACTERISTICS (Per Diode)

Symbol	Characteristic	Condition	Min	Тур	Мах	Unit
V _F	Instantaneous Forward Voltage (Note 3)	$\begin{split} I_F &= 15 \text{ Amp, } T_J = 25^\circ\text{C} \\ I_F &= 15 \text{ Amp, } T_J = 125^\circ\text{C} \\ I_F &= 30 \text{ Amp, } T_J = 25^\circ\text{C} \\ I_F &= 30 \text{ Amp, } T_J = 125^\circ\text{C} \end{split}$		- 0.50 - 0.65	0.62 0.57 0.82 0.72	V
I _R	Instantaneous Reverse Current (Note 3)	Rated dc Voltage, $T_J = 25^{\circ}C$ Rated dc Voltage, $T_J = 125^{\circ}C$	-	_ 9.0	0.2 25	mA

3. Pulse Test: Pulse Width = 300 $\mu s,$ Duty Cycle \leq 2.0%.

MBR2535CTG, MBR2545CTG



8.0

4.0

SQUARE WAVE

SQUARE WAVE

dc

T_C, CASE TEMPERATURE (°C) Figure 3. Current Derating, Per Device

SQUARE WAVE

8.0

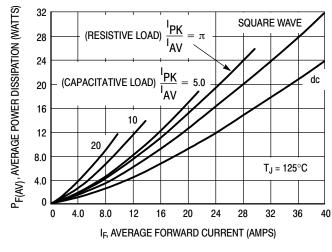
4.0

RATED VOLTAGE APPLIED

 $R_{\theta JC}$ = 1.5°C/W

Figure 4. Current Derating, Per Device

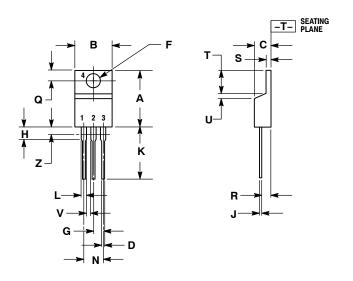
T_A, AMBIENT TEMPERATURE (°C)





PACKAGE DIMENSIONS

TO-220 CASE 221A-09 ISSUE AF



	INCHES MIN MAX		MILLIMETER	
DIM			MIN	MAX
Α	0.570	0.620	14.48	15.75
В	0.380	0.405	9.66	10.28
С	0.160	0.190	4.07	4.82
D	0.025	0.035	0.64	0.88
F	0.142	0.161	3.61	4.09
G	0.095	0.105	2.42	2.66
Н	0.110	0.155	2.80	3.93
J	0.014	0.025	0.36	0.64
Κ	0.500	0.562	12.70	14.27
L	0.045	0.060	1.15	1.52
Ν	0.190	0.210	4.83	5.33
Q	0.100	0.120	2.54	3.04
R	0.080	0.110	2.04	2.79
S	0.045	0.055	1.15	1.39
Т	0.235	0.255	5.97	6.47
U	0.000	0.050	0.00	1.27
V	0.045		1.15	
Ζ		0.080		2.04
PIN	1. ANO 2. CAT 3. ANO	HODE		

DIMENSIONING AND TOLERANCING PER ANSI

DIMENSION Z DEFINES A ZONE WHERE ALL

Y14.5M, 1982. CONTROLLING DIMENSION: INCH.

NOTES:

1

2

3.

SWITCHMODE is a trademark of Semiconductor Components Industries, LLC.

ON Semiconductor and IIII are registered trademarks of Semiconductor Components Industries, LLC (SCILLC). SCILLC reserves the right to make changes without further notice to any products herein. SCILLC makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does SCILLC assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. "Typical" parameters which may be provided in SCILLC data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. SCILLC does not convey any license under its patent rights nor the rights of others. SCILLC products are not designed, intended, or authorized for use as components in systems intended for surgical implant into the body, or other application in which the failure of the SCILLC product culd create a situation where personal injury or death may occur. Should Buyer purchase or use SCILLC products for any such unintended or unauthorized application, Buyer shall indemnify and hold SCILLC and its officers, employees, subsidiaries, and distributors harmless against all claims, costs, damages, and expenses, and reasonable attorney fees arising out of, directly or indirectly, any claim of personal injury or death agsociated with such unintended or unauthorized use, even if such claim alleges that SCILLC was negligent regarding the design or manufacture of the part. SCILLC is an Equal Opportunit/Affirmative Action Employer. This literature is subject to all applicable copyright laws and is not for resale in any manner.

PUBLICATION ORDERING INFORMATION

LITERATURE FULFILLMENT:

Literature Distribution Center for ON Semiconductor P.O. Box 5163, Denver, Colorado 80217 USA Phone: 303–675–2175 or 800–344–3860 Toll Free USA/Canada Fax: 303–675–2176 or 800–344–3867 Toll Free USA/Canada Email: orderlit@onsemi.com N. American Technical Support: 800–282–9855 Toll Free USA/Canada Europe, Middle East and Africa Technical Support:

Phone: 421 33 790 2910 Japan Customer Focus Center Phone: 81–3–5773–3850 ON Semiconductor Website: www.onsemi.com

Order Literature: http://www.onsemi.com/orderlit

For additional information, please contact your local Sales Representative